Silicon Diffused Power Transistor BU2530AW

GENERAL DESCRIPTION

New generation, high-voltage, high-speed switching npn transistor in a plastic envelope intended for use in horizontal deflection circuits of large screen colour television receivers up to 32 kHz.

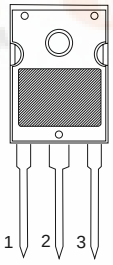
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	V_{BE} = 0	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	800	V
I_C	Collector current (DC)		-	16	A
I_{CM}	Collector current peak value		-	40	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25$ ˚C	-	125	W
V_{CEsat}	Collector-emitter saturation voltage	I_C = 9.0 A; I_B = 1.64 A	-	5.0	V
I_{Csat}	Collector saturation current		9	-	A
t_s	Storage time	I_{Csat} = 9.0 A; $I_{B(end)}$ = 1.3 A	3.5	4.5	µs

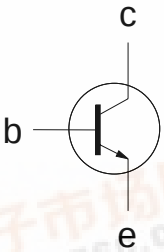
PINNING - SOT429

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	V_{BE} = 0 V	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	800	V
I_C	Collector current (DC)		-	16	A
I_{CM}	Collector current peak value		-	40	A
I_B	Base current (DC)		-	10	A
I_{BM}	Base current peak value		-	15	A
$-I_{B(AV)}$	Reverse base current	average over any 20 ms period	-	200	mA
$-I_{BM}$	Reverse base current peak value [1]		-	10	A
P_{tot}	Total power dissipation	$T_{mb} \leq$ 25 ˚C	-	125	W
T_{stg}	Storage temperature		-55	150	˚C
T_j	Junction temperature		-	150	˚C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Junction to mounting base	-	-	1.0	K/W
$R_{th\ j\text{-}a}$	Junction to ambient	in free air	45	-	K/W

1 Turn-off current.

STATIC CHARACTERISTICS

T_{mb} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}	Collector cut-off current [2]	V_{BE} = 0 V; V_{CE} = $V_{CESMmax}$	-	-	1.0	mA
I_{CES}		V_{BE} = 0 V; V_{CE} = $V_{CESMmax}$; T_j = 125 ˚C	-	-	2.0	mA
I_{EBO}	Emitter cut-off current	V_{EB} = 7.5 V; I_C = 0 A	-	-	1.0	mA
BV_{EBO}	Base-emitter breakdown voltage	I_B = 1 mA	7.5	14	-	V
V_{CEsat}	Collector-emitter saturation voltage	I_C = 9.0 A; I_B = 1.64 A	-	-	5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C = 9.0 A; I_B = 1.64 A	0.825	0.91	1.0	V
h_{FE}	DC current gain	I_C = 1 A; V_{CE} = 5 V	9	17	27	
h_{FE}		I_C = 9 A; V_{CE} = 5 V	5.5	8	10	

DYNAMIC CHARACTERISTICS

T_{mb} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
	Switching times (32 kHz line deflection dynamic test circuit).	I_{Csat} = 9.0 A; L_C = 200 µH; C_{fb} = 13 nF; V_{CC} = 138 V; $I_{B(end)}$ = 1.3 A; $-I_{BM}$ = 4.5 A; $-V_{BB}$ = 4 V; L_B = 1 µH			
t_s	Turn-off storage time		3.5	4.5	µs
t_f	Turn-off fall time		0.14	0.25	µs

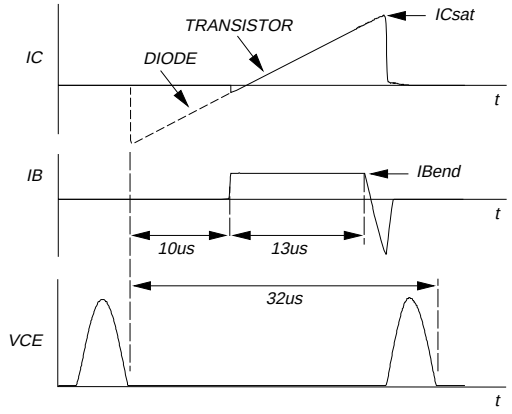


Fig.1. Switching times waveforms.

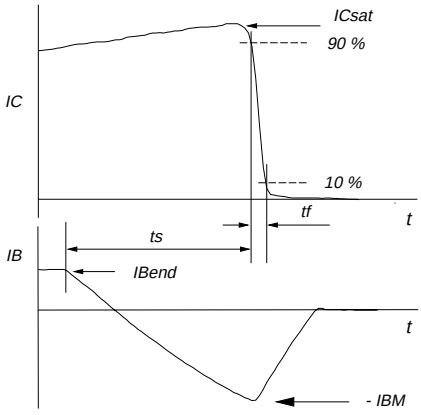


Fig.2. Switching times definitions.

2 Measured with half sine-wave voltage (curve tracer).

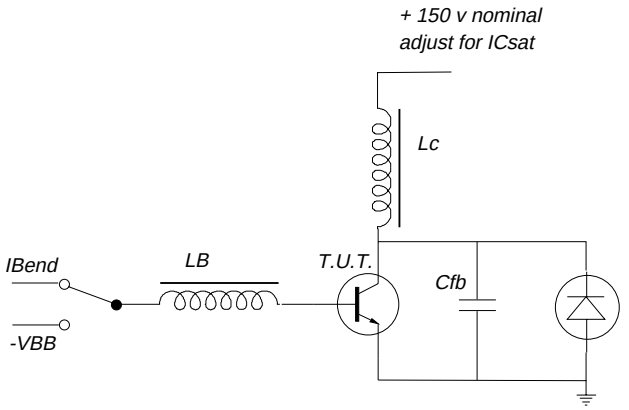


Fig.3. Switching times test circuit.

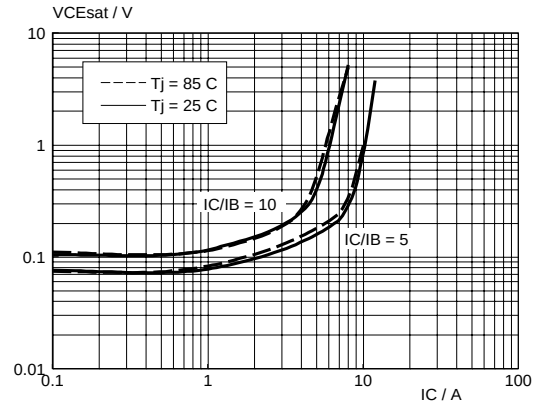


Fig.6. Typical collector-emitter saturation voltage. $V_{CE}sat = f(I_C)$; parameter I_C/I_B

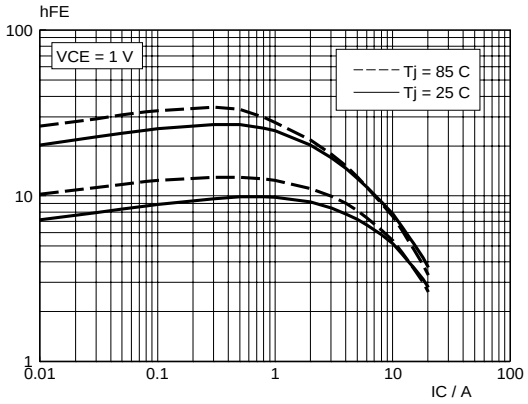


Fig.4. High and low DC current gain. $h_{FE} = f(I_C)$ $V_{CE} = 1$ V

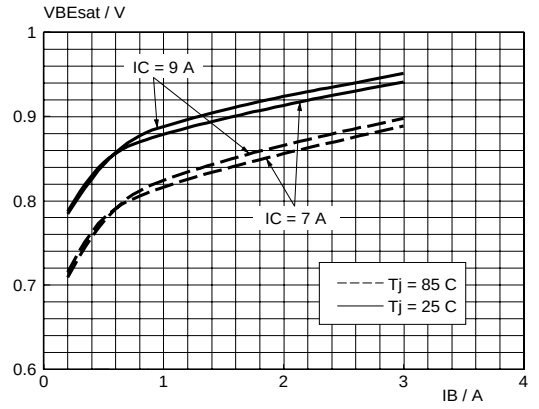


Fig.7. Typical base-emitter saturation voltage. $V_{BE}sat = f(I_B)$; parameter I_C

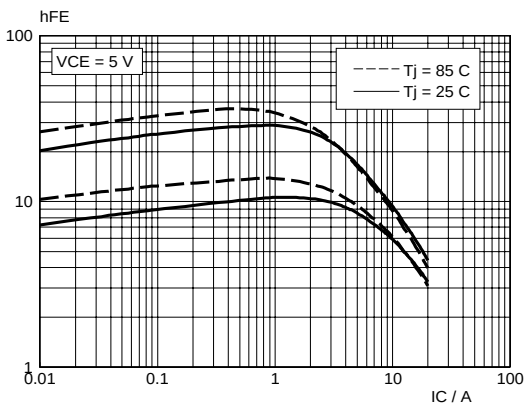


Fig.5. High and low DC current gain. $h_{FE} = f(I_C)$ $V_{CE} = 5$ V

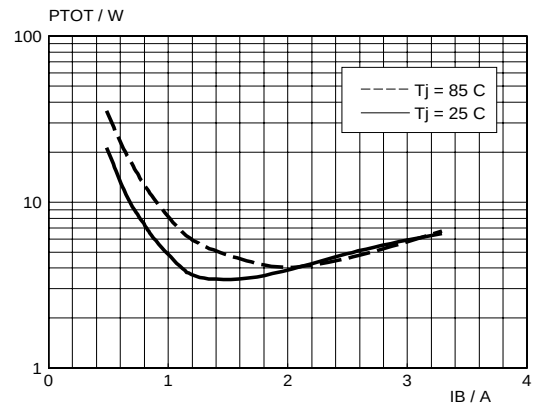


Fig.8. Typical turn-off losses. $P_{TOT} = f(I_B)$; parameter I_C; f = 32 kHz

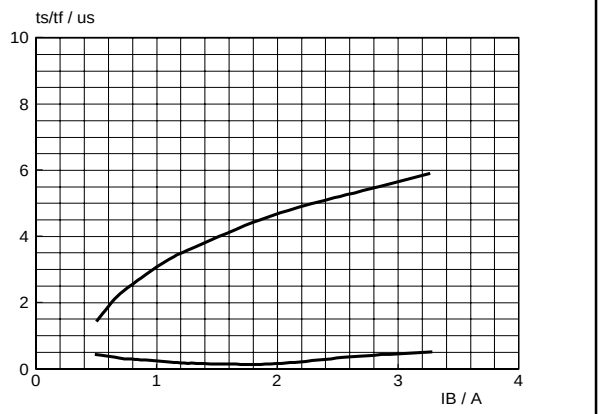


Fig.9. Typical collector storage and fall time. ts = f (I_B); tf = f (I_B); parameter I_C; T_j = 85˚C; f = 32 kHz

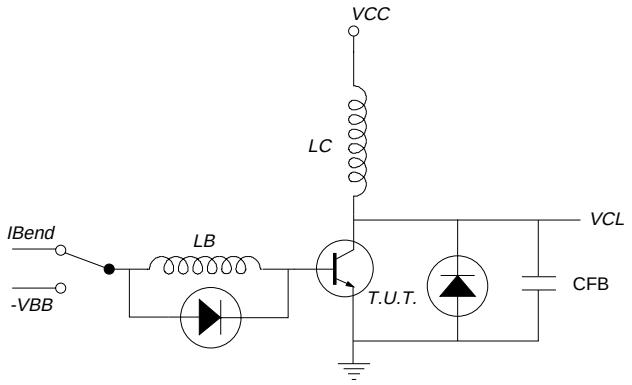


Fig.12. Test Circuit RBSOA. V_{CC} = 150 V; $-V_{BB}$ = 1 - 5 V; L_C = 1.5 mH; V_{CL} = 1450 V; L_B = 1 - 3 µH; C_{FB} = 1 - 10 nF; $I_{B(end)}$ = 1.3 - 2.6 A

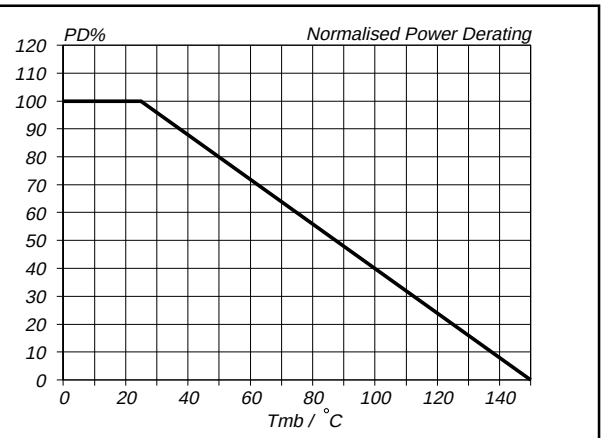


Fig.10. Normalised power dissipation. PD% = 100·P_D/$P_{D\ 25˚C}$ = f (T_{mb})

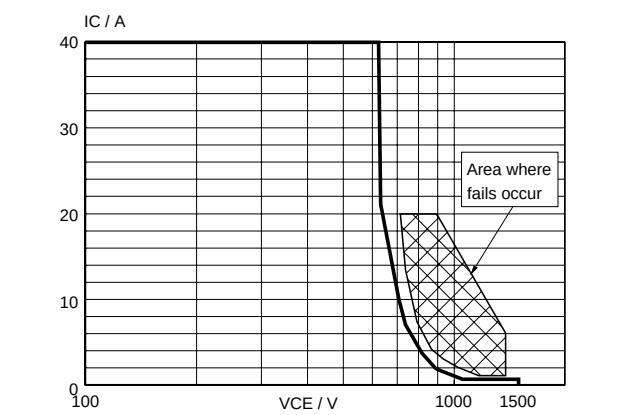


Fig.13. Reverse bias safe operating area. $T_j \leq T_{jmax}$

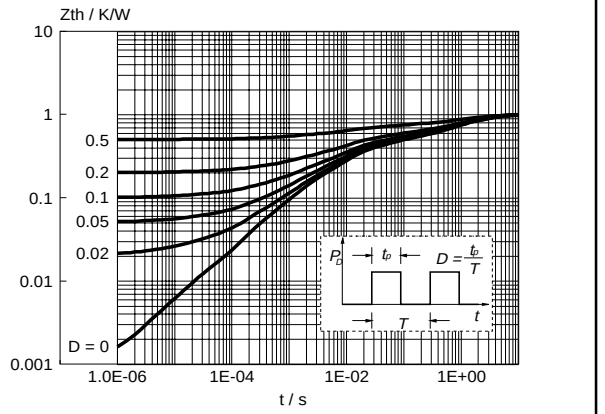


Fig.11. Transient thermal impedance. $Z_{th\ j\text{-}mb}$ = f(t); parameter D = t_p/T

MECHANICAL DATA

Dimensions in mm

Net Mass: 5 g

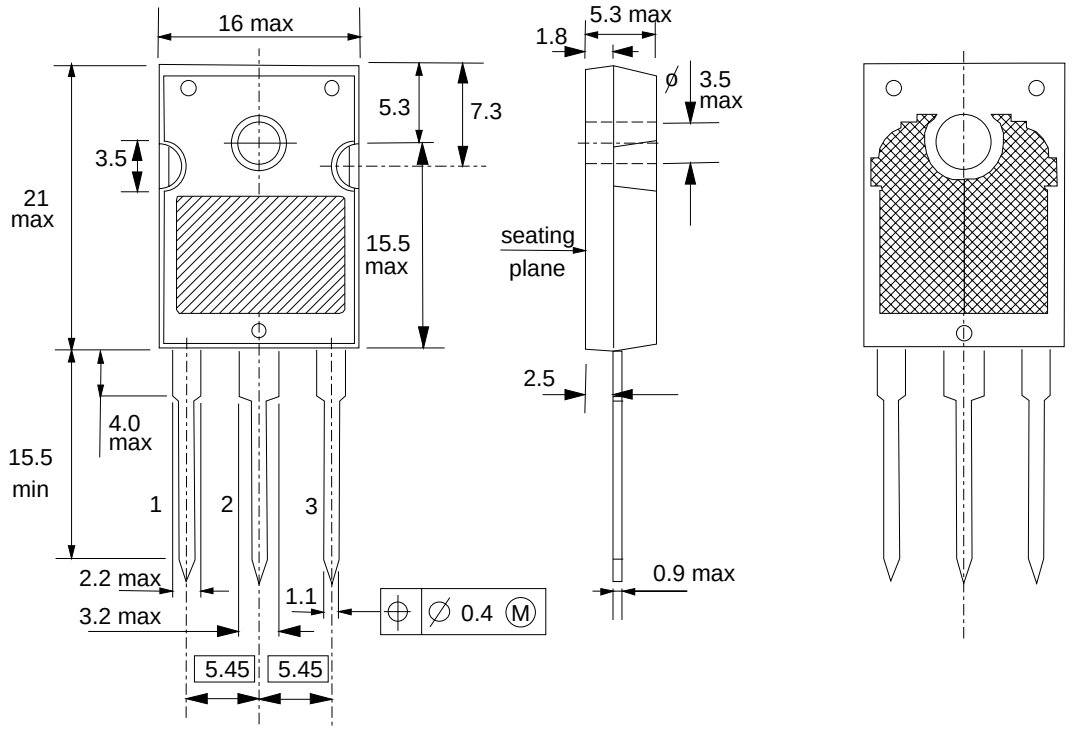


Fig.14. SOT429; pin 2 connected to mounting base.

Notes

1. Refer to mounting instructions for SOT429 envelope.
2. Epoxy meets UL94 V0 at 1/8".

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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